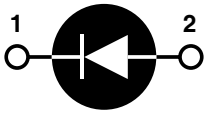
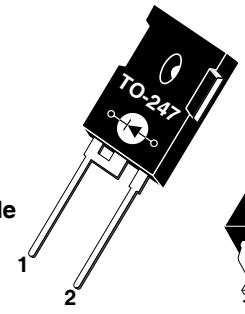
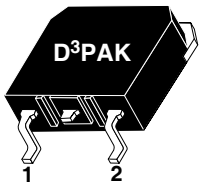


1 - Cathode
2 - Anode
Back of Case - Cathode





Microsemi
POWER PRODUCTS GROUP

APT60S20B(G) 200V 75A
APT60S20S(G) 200V 75A

*G Denotes RoHS Compliant, Pb Free Terminal Finish.

HIGH VOLTAGE SCHOTTKY DIODE

PRODUCT APPLICATIONS

- Parallel Diode
  - -Switchmode Power Supply
  - -Inverters
- Free Wheeling Diode
  - -Motor Controllers
  - -Converters
- Snubber Diode
- Uninterruptible Power Supply (UPS)
- 48 Volt Output Rectifiers
- High Speed Rectifiers

PRODUCT FEATURES

- Ultrafast Recovery Times
- Soft Recovery Characteristics
- Popular TO-247 Package or Surface Mount D³PAK Package
- Low Forward Voltage
- High Blocking Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Low Losses
- Low Noise Switching
- Cooler Operation
- Higher Reliability Systems
- Increased System Power Density

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT60S20B_S(G)	UNIT
V_R	Maximum D.C. Reverse Voltage	200	Volts
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
V_{RWM}	Maximum Working Peak Reverse Voltage		
$I_F(AV)$	Maximum Average Forward Current (T_C = 123°C, Duty Cycle = 0.5)	75	Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)	208	
I_{FSM}	Non-Repetitive Forward Surge Current (T_J = 45°C, 8.3ms)	600	
T_J,T_{STG}	Operating and StorageTemperature Range	-55 to 150	°C
T_L	Lead Temperature for 10 Sec.	300	
E_{VAL}	Avalanche Energy (2A, 30mH)	60	mJ

STATIC ELECTRICAL CHARACTERISTICS

Symbol			MIN	TYP	MAX	UNIT
V_F	Forward Voltage	I_F = 60A		.83	.90	Volts
		I_F = 120A		.98		
		I_F = 60A, T_J = 125°C		.72		
I_{RM}	Maximum Reverse Leakage Current	V_R = 200V			1	mA
		V_R = 200V, T_J = 125°C			25	
C_T	Junction Capacitance, V_R = 200V			300		pF

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DYNAMIC CHARACTERISTICS

APT60S20B_S(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -200A/µs V_R = 133V, T_C = 25°C	-	55		ns
Q_{rr}	Reverse Recovery Charge		-	160		nC
I_{RRM}	Maximum Reverse Recovery Current		-	5	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -200A/µs V_R = 133V, T_C = 125°C	-	100		ns
Q_{rr}	Reverse Recovery Charge		-	490		nC
I_{RRM}	Maximum Reverse Recovery Current		-	10	-	Amps
t_{rr}	Reverse Recovery Time	I_F = 60A, di_F/dt = -700A/µs V_R = 133V, T_C = 125°C	-	80		ns
Q_{rr}	Reverse Recovery Charge		-	1100		nC
I_{RRM}	Maximum Reverse Recovery Current		-	27		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			.30	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			40	
W_T	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

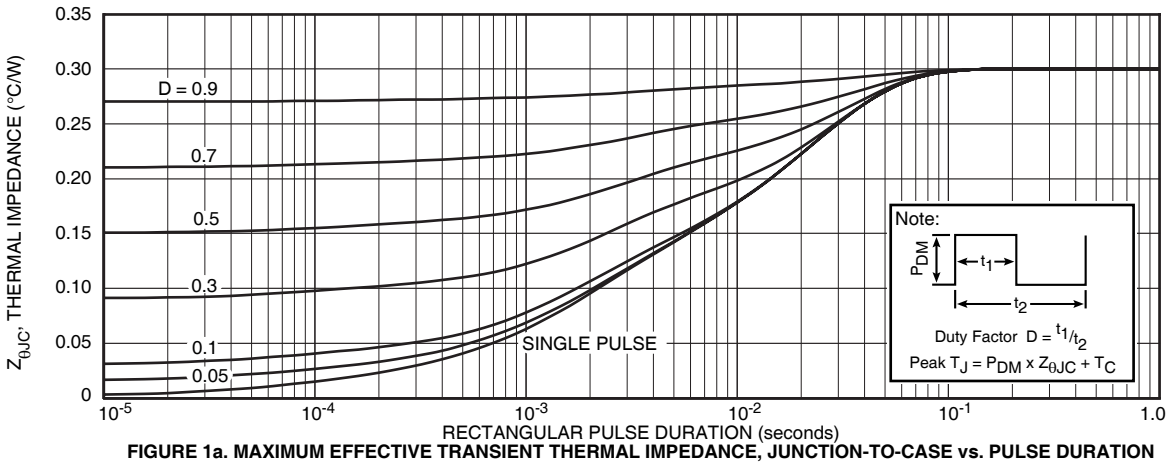


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

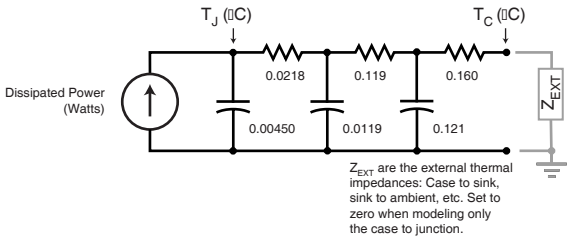


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

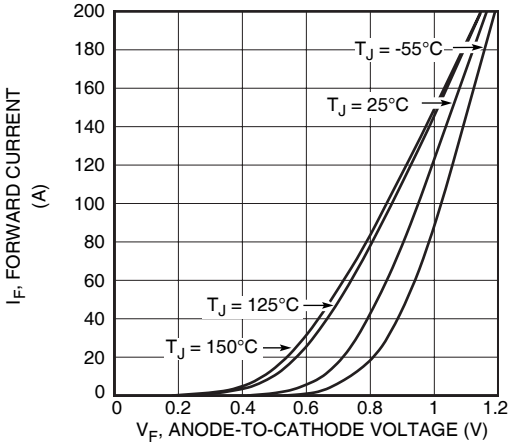


Figure 2. Forward Current *vs.* Forward Voltage

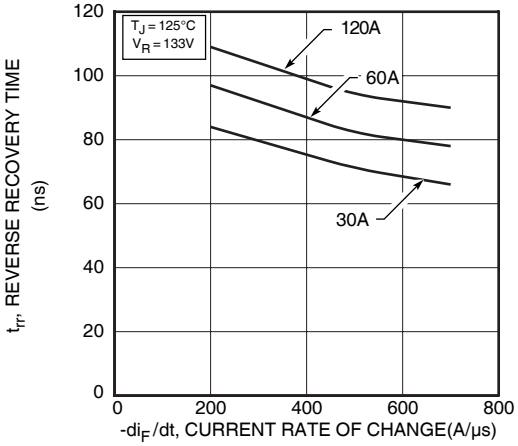


Figure 3. Reverse Recovery Time *vs.* Current Rate of Change

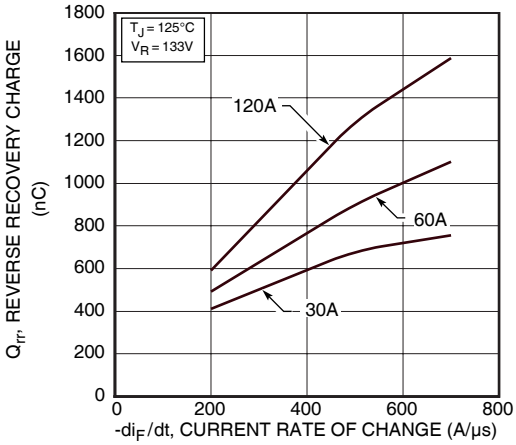


Figure 4. Reverse Recovery Charge *vs.* Current Rate of Change

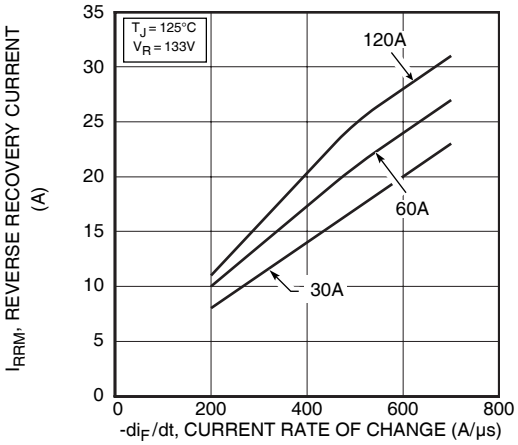


Figure 5. Reverse Recovery Current *vs.* Current Rate of Change

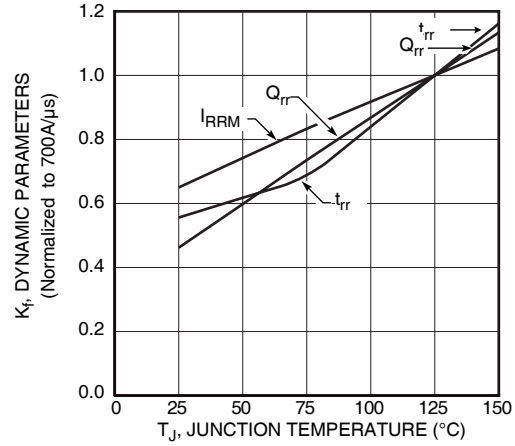


Figure 6. Dynamic Parameters *vs.* Junction Temperature

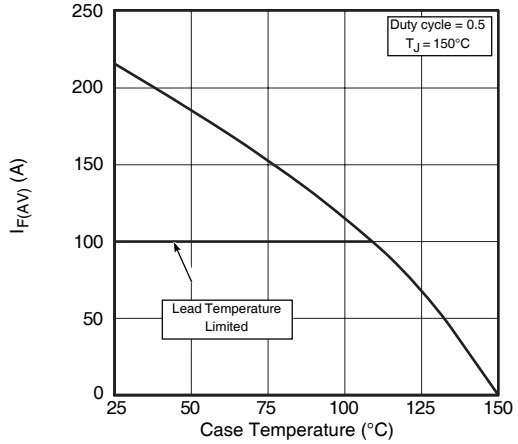


Figure 7. Maximum Average Forward Current *vs.* CaseTemperature

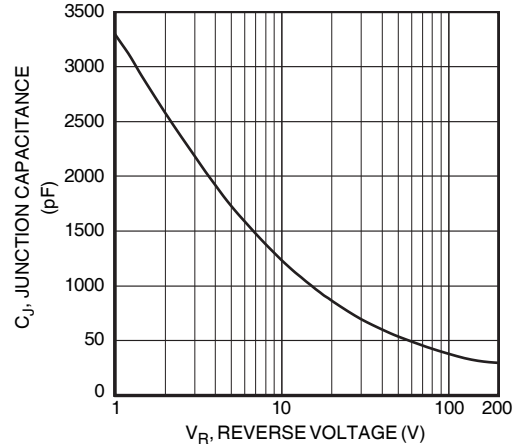


Figure 8. Junction Capacitance *vs.* Reverse Voltage

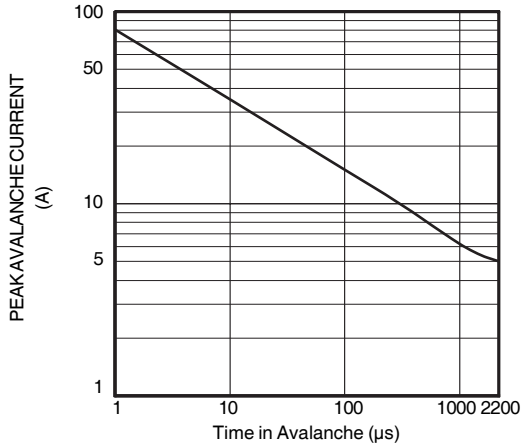


Figure 9. Single Pulse UIS SOA

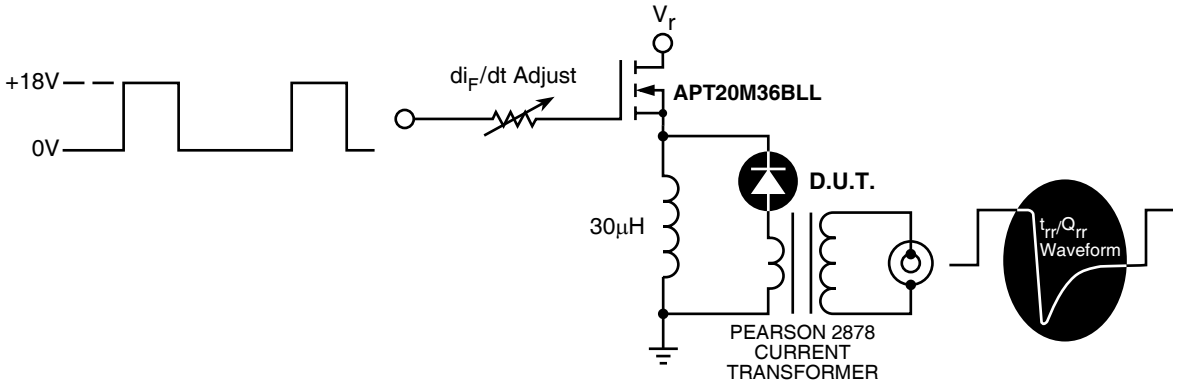
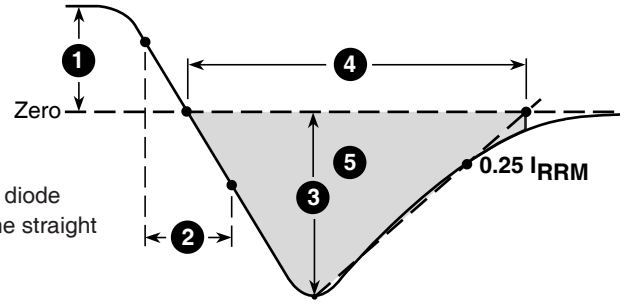


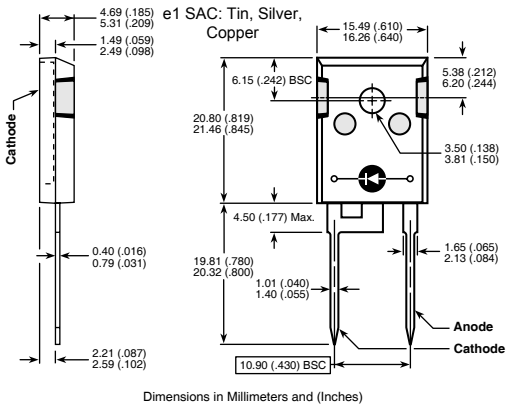
Figure 9. Diode Test Circuit



1. I_F - Forward Conduction Current
2. di_F/dt - Rate of Diode Current Change Through Zero Crossing.
3. I_{RRM} - Maximum Reverse Recovery Current.
4. t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \bullet I_{RRM}$ passes through zero.
5. Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr}.

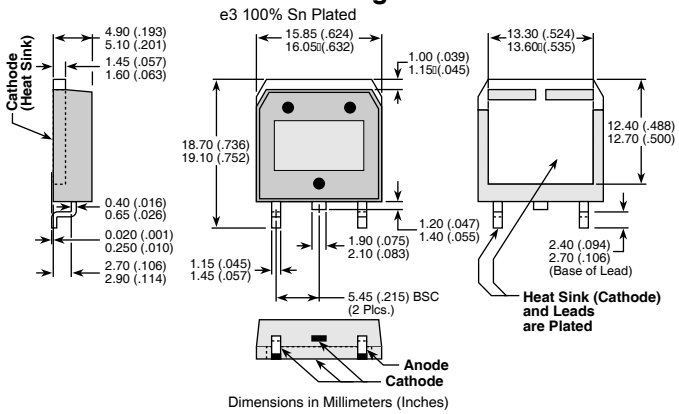
Figure 10, Diode Reverse Recovery Waveform and Definitions

TO-247 Package Outline



Dimensions in Millimeters and (Inches)

D^{3}PAK Package Outline



Dimensions in Millimeters (Inches)

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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